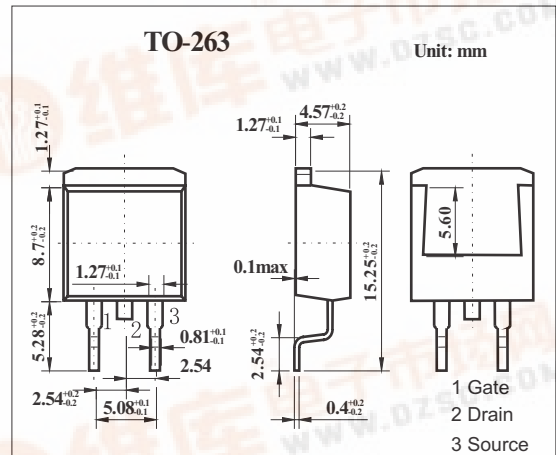
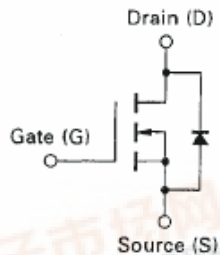


SMD Type MOSFET

MOS Field Effect Power Transistor  
2SK2133

■ Features

- Low on-resistance  
RDS(on)=0.21 Ω MAX.@VGS=10V, ID=8.0A
- Low Ciss Ciss=1090 pF TYP.
- High avalanche capabil



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Drain to source voltage	V <sub>DSS</sub>	250	V
Gate to source voltage	V <sub>GSS</sub>	± 30	V
Drain current	I <sub>D</sub>	± 16	A
	I <sub>DP</sub> *	± 64	A
Power dissipation TA=25°C Tc=25°C	P <sub>D</sub>	1.5	W
		75	W
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

\* PW ≤ 10 μ s, Duty Cycle ≤ 1%

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit	
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> =250V, V <sub>GS</sub> =0			100	μ A	
Gate leakage current	I <sub>GSS</sub>	V <sub>GS</sub> =± 30V, V <sub>DS</sub> =0			± 10	μ A	
Gate to source cutoff voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	2.0		4.0	V	
Forward transfer admittance	Y <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =8.0A	4.0			S	
Drain to source on-state resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =8.0A		0.2	0.26	Ω	
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =0, f=1MHZ		1090		pF	
Output capacitance	C <sub>oss</sub>				420		pF
Reverse transfer capacitance	C <sub>rss</sub>				80		pF
Turn-on delay time	t <sub>d(on)</sub>				20		ns
Rise time	t <sub>r</sub>	I <sub>D</sub> =8.0A, V <sub>GS(on)</sub> =10V, R <sub>L</sub> =18.75 Ω, R <sub>G</sub> =10 Ω, V <sub>DD</sub> =150V		40		ns	
Turn-off delay time	t <sub>d(off)</sub>				60		ns
	t <sub>f</sub>				20		ns

